

SCOPE: Complete, 8-Channel, 12-Bit Data Acquisition Systems

<u>Device Type</u>	<u>Generic Number</u>		
01	MAX180AM(x)/883B	04	MAX181AM(x)/883B
02	MAX180BM(x)/883B	05	MAX181BM(x)/883B
03	MAX180CM(x)/883B	06	MAX181CM(x)/883B

Case Outline(s). The case outlines shall be designated in Mil-Std-1835 and as follows:

<u>Outline Letter</u>	<u>Mil-Std-1835</u>	<u>Case Outline</u>	<u>Package Code</u>
JL	GDIP1-T40	40 LEAD CERDIP	J40
DL	CDIP2-T40	40-Pin SIDEBRAZE	D40

Absolute Maximum Ratings

V_{DD} to DGND	-0.3V to +7V
V_{SS} to DGND	-0.3V to -17V
AGND to DGND	-0.3V to ($V_{DD}+0.3V$)
AIN ₋ , MUXOUT, ADCIN, REFADJ, OFFADJ to REFIN	-0.3V to ($V_{DD}+0.3V$)
OFFADJ to REFIN	-0.3V to ($V_{DD}+0.3V$)
REFIN to DGND	+0.3V to ($V_{SS}-0.3V$)
$\overline{CS}$, $\overline{WR}$, $\overline{RD}$, CLK A2-A0, BIP, DIFF, HBEN to DGND.....	-0.3V to ($V_{DD}+0.3V$)
$\overline{BUSY}$, D0-D11 to DGND	-0.3V to ($V_{DD}+0.3V$)
Lead Temperature (soldering, 10 seconds)	+300°C
Storage Temperature	-65°C to +160°C
Continuous Power Dissipation	$T_A=+70^\circ\text{C}$
40 pin CERDIP(derate 20mW/°C above +70°C)	1600mW
40 pin Sidebrazed(derate 25mW/°C above +70°C)	2000mW
Junction Temperature T_J	+150°C
Thermal Resistance, Junction to Case, θ_{JC}	
40 pin CERDIP.....	25°C/W
40 pin Sidebrazed	15°C/W
Thermal Resistance, Junction to Ambient, θ_{JA} :	
40 pin CERDIP.....	50°C/W
40 pin Sidebrazed	40°C/W

Recommended Operating Conditions

Ambient Operating Range (T_A)	-55°C to +125°C
Supply Voltage (V_{CC}).....	+4.75V to +5.25V
Supply Voltage (V_{SS}).....	-11.4V to -15.75V

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TABLE 1. ELECTRICAL TESTS:

TEST	Symbol	CONDITIONS -55 °C ≤ T _A ≤ +125°C V _{DD} =+5V±5%, V _{SS} =-12V ±5% or -15V±5%, REFIN=-5V, f _{CLK} =1.6MHz 1/ Unless otherwise specified	Group A Subgroup	Device type	Limits Min	Limits Max	Units
ACCURACY 2/							
Resolution	N			All	12		Bits
Integral Nonlinearity	INL		1,2,3	01,04 02,03, 05,06		±0.5 ±1.0	LSB
Differential Nonlinearity	DNL		1,2,3	All		±1.0	LSB
Unipolar Offset Error	V _{OS}	NOTE 3	1,2,3	All		±4.0	LSB
Bipolar Offset Error	AE	NOTE 3	1,2,3	All		±6.0	LSB
Unipolar Gain Error			1,2,3	All		±10.0	LSB
Bipolar Gain Error			1,2,3	All		±15.0	LSB
Gain Error Tempco		NOTE 4,5		All		±5.0	ppm/°C
DYNAMIC TESTS		NOTE 2					
Signal-to-Noise Plus Distortion Ratio	SINAD	10kHz input signal, 100kHz sampling rate, bipolar mode	9	All	70		dB
Total Harmonic Distortion	THD	10kHz input signal, 100kHz sampling rate, bipolar mode. Up to the 5th harmonic.	9	All		-80	dB
Spurious Free Dynamic Range	SFDR		9	All	80		dB
Full-Power Sampling Bandwidth NOTE 5		In track mode, under-sampled waveform		All		6	MHz
Track-and-Hold Acquisition Time	t _{ACQ}	NOTE 5		All	1.875		μs
Conversion Time	t _{CONV}	Asynchronous hold mode Note 5			7.500	8.125	μs
		ROM Slow-Memory and I/O Port Modes; 15-16 clock cycles	9,10,11	All	9.375	10.0	
ANALOG INPUT							
Voltage Range		AIN ₋ , MUXOUT, and ADCIN	1,2,3	All	REFIN	V _{DD}	V
Unipolar, Single-Ended Range		AIN ₋ to AGND	1,2,3	All	0	5.0	V
Unipolar, Differential Range		AIN ₊ to AIN ₋	1,2,3	All	0	5.0	V
Bipolar, Single-Ended Range		AIN ₋ to AGND	1,2,3	All	-2.5	2.5	V
Bipolar, Differential Range		AIN ₊ to AIN ₋	1,2,3	All	-2.5	2.5	V
Input Current		AIN ₋	1,2,3	01,02,03		±1.0	μA
Input Current		ADCIN ₋	1,2,3	04,05,06		±0.1	μA
Mux-On Resistance	R _{ON}	AIN ₋ =2.5V, I _{MUXOUT} =1.25mA	1,2,3	04,05,06		2	kΩ
Mux-On Leakage Current	I _{ON}	AIN ₋ =MUXOUT=±5V	1,2,3	04,05,06		±100	nA
Mux-Off Leakage Current	I _{IN} (OFF) I _{OUT} (OFF)	AIN ₋ =±5V, V _{OUT} =±5V AIN ₋ =±5V, V _{OUT} =±5V	1,2,3	04,05,06		±100	nA

TEST	Symbol	CONDITIONS -55 °C ≤ T _A ≤ +125 °C V _{DD} = +5V ± 5%, V _{SS} = -12V ± 5% or -15V ± 5%, REFIN = -5V, f _{CLK} = 1.6MHz ^{1/} Unless otherwise specified	Group A Subgroup	Device type	Limits Min	Limits Max	Units
Input Capacitance ^{5/}	C _{IN}	AIN_, ADCIN MUXOUT		04,05,06		35 45	pF
REFERENCE INPUT							
Input Range		NOTE 5		All	-4.92	-5.08	V
Input Current			1,2,3	All		-2	mA
Input Resistance			1,2,3	All	2.5		kΩ
REFERENCE OUTPUT							
V _{REF} Output Voltage			1	All	-4.98	-5.02	V
V _{REF} Output Tempco		NOTE 6	1,2,3	01,02, 04,05		25	ppm/°C
V _{REF} Output Tempco		NOTE 6	1,2,3	03,06		45	ppm/°C
Load Regulation NOTE 7		0mA < I _{OUT} < 5mA	1	All		1.0	mV/mA
REFADJ, OFFADJ							
Input Current		V _{REFADJ} , V _{OFFADJ} = V _{DD} to REFIN	1,2,3	All		±1	μA
Disable Threshold			1,2,3	All	4.5		V
REFADJ Adjustment Range		REFIN < REFADJ < AGND	1,2,3	All	±60		mV
OFFADJ Adjustment Range		REFIN < REFADJ < AGND	1,2,3	All	±15		LSB
LOGIC INPUTS							
Logic High Voltage	V _{IH}	MODE	1,2,3	All	4.5		V
		CLK, A2-A0, DIFF, BIP, HBEN, $\overline{\text{CS}}$, $\overline{\text{RD}}$, $\overline{\text{WR}}$			2.4		
Logic Low Voltage	V _{IL}	MODE	1,2,3	All		0.5	V
		CLK, A2-A0, DIFF, BIP, HBEN, $\overline{\text{CS}}$, $\overline{\text{RD}}$, $\overline{\text{WR}}$				0.8	
Input Mid-Level Voltage	V _{MID}	MODE	1,2,3	All	1.5	3.5	V
Input Floating Voltage	V _{FLT}	MODE NOTE 5		All		2.5	V
Input Current	I _{IN}	MODE	1,2,3	All		±100	μA
Input Current	I _{IN}	CLK, A2-A0, DIFF, BIP, HBEN, $\overline{\text{CS}}$, $\overline{\text{RD}}$, $\overline{\text{WR}}$	1 2,3	All		±1 ±10	μA
Input Capacitance	C _{IN}	NOTE 5		All		15	pF
LOGIC OUTPUTS							
Output High Voltage	V _{OH}	I _{SOURCE} = 360μA, D11-D0, $\overline{\text{RDY}}$, $\overline{\text{BUSY}}$	1,2,3	All	4.0		V
Output Low Voltage	V _{OL}	I _{SINK} = 1.6mA, D11-D0, $\overline{\text{RDY}}$, $\overline{\text{BUSY}}$	1,2,3	All		0.4	V
Floating-State Leakage Current	I _{LKG}	D11-D0, V _{OUT} = 0V to V _{DD}	1,2,3	All		±10	μA
Floating-State Output Capacitance NOTE 5	C _{OUT}		1,2,3			15	pF

TEST	Symbol	CONDITIONS -55 °C ≤ T _A ≤ +125 °C V _{DD} =+5V±5%, V _{SS} =-12V ±5% or -15V±5%, REFIN=-5V, f _{CLK} =1.6MHz ^{1/} Unless otherwise specified	Group A Subgroup	Device type	Limits Min	Limits Max	Units
POWER REQUIREMENTS							
Supply Voltage NOTE 1	V _{DD}		1,2,3	All	4.75	5.25	V
	V _{SS}				-11.40	-15.75	
Supply Current	I _{DD}	V _{DD} =5V	1,2,3	All		7.0	mA
	I _{SS}	V _{SS} =-12V				10.0	
Power Dissipation	PD	V _{DD} =5V, V _{SS} =-15V	1,2,3	All		155	mW
Power-Supply Rejection with Internal Reference	PSR	Input near FS, V _{SS} =-12V, V _{DD} =4.75V to 5.25V	1,2,3	All		±1.0	LSB
Power-Supply Rejection with Internal Reference	PSR	Input near FS, V _{DD} =5V, V _{SS} =-14.25V to -15.75V	1,2,3	All		±0.5	LSB
Power-Supply Rejection with Internal Reference	PSR	Input near FS, V _{DD} =5V, V _{SS} =-11.4V to -12.6V	1,2,3	All		±0.5	LSB
TIMING		NOTE 8					
$\overline{\text{CS}}$ to $\overline{\text{RD}}$ Setup time	t ₁	NOTE 5		All	0		ns
$\overline{\text{CS}}$ to $\overline{\text{RD}}$ Hold time	t ₂		9,10,11	All	0		ns
$\overline{\text{CS}}$ to $\overline{\text{WR}}$ Setup time	t ₃		9,10,11	All	0		ns
$\overline{\text{CS}}$ to $\overline{\text{WR}}$ Hold time	t ₄	NOTE 5		All	0		ns
$\overline{\text{WR}}$ Low Pulse Width	t ₅		9,10,11	All	120		ns
$\overline{\text{WR}}$ High Pulse Width	t ₆	MODE=0 or 1, NOTE 5		All	200		ns
DATA IN to $\overline{\text{WR}}$ Setup Time	t ₇		9 10,11	All	80 120		ns
DATA IN to $\overline{\text{WR}}$ Hold Time	t ₈		9,10,11	All	0		ns
$\overline{\text{WR}}$ Rising to $\overline{\text{BUSY}}$ Delay	t ₉	C _L =50pF, MODE=1	9 10,11	All		160 200	ns
$\overline{\text{WR}}$ Falling to $\overline{\text{BUSY}}$ Delay	t ₁₀	C _L =50pF, MODE=open	9 10,11	All		220 280	ns
$\overline{\text{RD}}$ Low Pulse Width	t ₁₁		9 10,11	All	100 150		ns
$\overline{\text{RD}}$ High Pulse Width	t ₁₂	NOTE 5		All	200		ns
DATA IN to $\overline{\text{RD}}$ Setup Time	t ₁₃		9 10,11	All	80 120		ns

TEST	Symbol	CONDITIONS -55 °C ≤ T _A ≤ +125°C V _{DD} =+5V±5%, V _{SS} =-12V ±5% or -15V±5%, REFIN=-5V, f _{CLK} =1.6MHz ^{1/} Unless otherwise specified	Group A Subgroup	Device type	Limits Min	Limits Max	Units
DATA IN to RD Hold Time	t ₁₄		9,10,11	All	0		ns
RD to BUSY Fall Delay	t ₁₅	C _L =50pF	9 10,11	All		150 200	ns
RD to Data Out Valid	t ₁₆	C _L =100pF, NOTE 9	9 10,11	All		100 150	ns
RD to Data Out Three-State	t ₁₇	NOTE 9, 10	9 10,11	All		50 75	ns
HBEN to RD or WR Setup Time	t ₁₈		9 10,11	All	80 120		ns
HBEN to RD or WR Hold Time	t ₁₉		9,10,11	All	0		ns
CS to READY Fall Delay	t ₂₀	C _L =50pF	9 10,11	All		110 150	ns
BUSY to Data Out Valid	t ₂₁	C _L =100pF, NOTE 9	9 10,11	All		125 170	ns
CS, RD, or WR to CLK Setup time for 15 clock conversion	t ₂₂	NOTE 5		All	220		ns
CS, RD, or WR to CLK Setup time for 16 clock conversion	t ₂₃	NOTE 5		All	0		ns

NOTE 1: Internal Reference Mode, Bipolar Mode, Slow-Memory Mode. Performance at power-supply tolerance limits guaranteed by power-supply rejection test.

NOTE 2: V_{DD}=+5V, V_{SS}=-15V, FS=+5V, REFIN=-5V.

NOTE 3: Typical change over temperature is ±1LSB.

NOTE 4: FS Tempco=ΔFS/ΔT, where ΔFS is full-scale change from 25°C to +125°C or -55°C.

NOTE 5: Guaranteed by design. Not subject to test.

NOTE 6: REFIN TC = ΔREFIN/ΔT, where ΔREFIN is reference voltage change from 25°C to +125°C or -55°C.

NOTE 7: Load current should remain constant during conversion. This current is in addition to the DAC input current.

NOTE 8: All inputs are 0V to +5V swing with t_R=t_F=5ns (10% to 90% of 5V) and timed from voltage level of +1.6V.

NOTE 9: t₁₆ and t₂₁ are measured with the load circuits of Figure 1 and defined as the time required for an output to cross 0.8V or 2.4V.

NOTE 10: t₁₇ is defined as the time required for the data lines to change 0.5V when the circuit load is as shown in Figure 2.

FIGURES 1 and 2: See Commercial Datasheet.

Package	ORDERING INFORMATION:		
40 pin Cerdip	MAX180AMJL/883B	MAX180BMJL/883B	MAX180CMJL/883B
40 pin Sidebrazed	MAX180AMDJL/883B	MAX180BMDJL/883B	MAX180CMDJL/883B

Package	ORDERING INFORMATION:		
40 pin CERDIP	MAX181AMJL/883B	MAX181BMJL/883B	MAX181CMJL/883B
40 pin Sidebraz	MAX181AMD L/883B	MAX181BMD L/883B	MAX181CMD L/883B

TERMINAL CONNECTIONS:

	MAX180	MAX181	
1	AIN0	AIN0	Analog Input to the MUX, 0V to +5V Unipolar, -2.5V to +2.5V bipolar
2	AIN1	AIN1	Analog Input, 0V to +5V Unipolar
3	AIN2	AIN2	Analog Input
4	AIN3	AIN3	Analog Input
5	AIN4	AIN4	Analog Input
6	AIN5	AIN5	Analog Input
7	AIN6	MUXOUT	Multiplexer Output (MAX181)
8	AIN7	ADCIN	Analog Input to Track and Hold (MAX181)
9	REFIN	REFIN	Reference Input
10	AGND	AGND	Analog Ground
11	REFOUT	REFOUT	-5V Reference Output
12	REFADJ	REFADJ	-5V Reference Adjust. Connect to V _{DD} if not required.
13	OFFADJ	OFFADJ	Offset adjust. Connect to V _{DD} if not required.
14	MODE	MODE	Interface Mode Select pin.
15	V _{SS}	V _{SS}	Negative Supply, -12V or -15V.
16	D11	D11	Three-State Data Outputs, MSB=D11
17	D10	D10	Three-State Data Outputs
18	D9	D9	Three-State Data Outputs
19	D8	D8	Three-State Data Outputs
20	GND	GND	Digital Ground
21	D7	D7	Three-State Data Outputs, LSB=D0
22	D6	D6	Three-State Data Outputs
23	D5	D5	Three-State Data Outputs
24	D4	D4	Three-State Data Outputs
25	D3	D3	Three-State Data Outputs
26	D2	D2	Three-State Data Outputs
27	D1	D1	Three-State Data Outputs
28	D0	D0	Three-State Data Outputs
29	CLKIN	CLKIN	Clock Input, TTL/CMOS compatible
30	HBEN	HBEN	High-Byte Enable Input
31	$\overline{\text{RD}}$	$\overline{\text{RD}}$	$\overline{\text{READ}}$ Input
32	$\overline{\text{WR}}$	$\overline{\text{WR}}$	$\overline{\text{WRITE}}$ Input (MODE=1 or Open) $\overline{\text{READY}}$ Output (MODE=0)
33	$\overline{\text{CS}}$	$\overline{\text{CS}}$	$\overline{\text{CHIP-SELECT}}$ Input
34	$\overline{\text{BUSY}}$	$\overline{\text{BUSY}}$	$\overline{\text{BUSY}}$ Output
35	DIFF	DIFF	Single-Ended Mode: DIFF=0, Differential Mode: DIFF=1
36	BIP	BIP	Unipolar Mode: BIP=0, Bipolar Mode: BIP=1
37	A0	A0	Multiplexer Channel Address Input: A2=MSB, A0=LSB
38	A1	A1	Multiplexer Channel Address Input: A2=MSB, A0=LSB
39	A2	A2	Multiplexer Channel Address Input: A2=MSB, A0=LSB
40	V _{DD}	V _{DD}	Positive Supply, +5V Input (substrate connected to V _{DD})

QUALITY ASSURANCE

Sampling and inspection procedures shall be in accordance with MIL-Prf-38535, Appendix A as specified in Mil-Std-883.

Screening shall be in accordance with Method 5004 of Mil-Std-883. Burn-in test Method 1015:

1. Test Condition, A, B, C, or D.
2. TA = +125°C minimum.
3. Interim and final electrical test requirements shall be specified in Table 2.

Quality conformance inspection shall be in accordance with Method 5005 of Mil-Std-883, including Groups A, B, C, and D inspection.

Group A inspection:

1. Tests as specified in Table 2.
2. Selected subgroups in Table 1, Method 5005 of Mil-Std-883 shall be omitted.

Group C and D inspections:

- a. End-point electrical parameters shall be specified in Table 1.
- b. Steady-state life test, Method 1005 of Mil-Std-883:
 1. Test condition A, B, C, D.
 2. TA = +125°C, minimum.
 3. Test duration, 1000 hours, except as permitted by Method 1005 of Mil-Std-883.

TABLE 2. ELECTRICAL TEST REQUIREMENTS

Mil-Std-883 Test Requirements	Subgroups per Method 5005, Table 1
Interim Electric Parameters Method 5004	1
Final Electrical Parameters Method 5005	1*, 2, 3, 4**, 9
Group A Test Requirements Method 5005	1, 2, 3, 4**, 9
Group C and D End-Point Electrical Parameters Method 5005	1

* PDA applies to Subgroup 1 only.

** Subgroup 4 shall be tested at initial qualification and upon redesign. Sample size will be 116 units.